

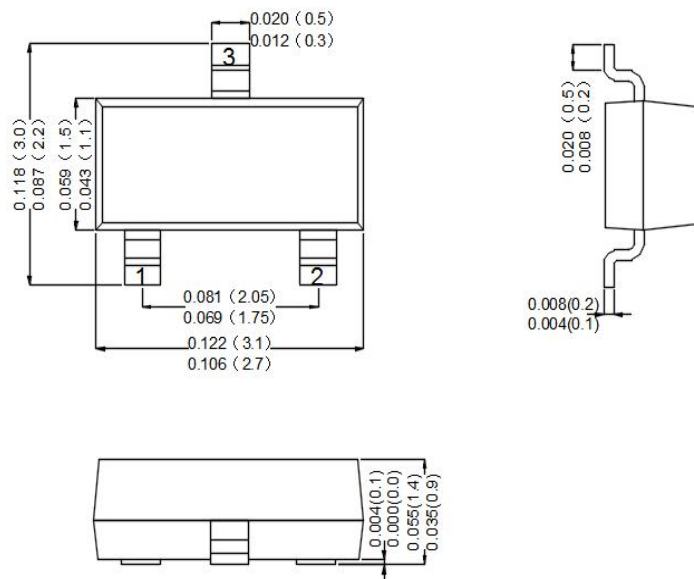


Features

SOT-23

Mechanical Data

- Case: Molded Plastic, SOT-23
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Plated Leads Solderable per MIL-STD-750, Method-2026.
- Marking: 491A
- Mounting Position : Any.
- Equivalent Circuit:



Dimensions in inches and (millimeters)

Maximum Ratings Maximum Ratings (Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Peak Pulse Current	I_{CM}	2	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_S	- 55 to + 1 0	°C



MMBT491A

NPN Silicon Epitaxial Planar Transistor

Electrical Characteristics (Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$ at $V_{CE} = 5\text{ V}$, $I_C = 500\text{ mA}$ at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ A}$	h_{FE} h_{FE} h_{FE}	300 300 200	- 900 -	- - -
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	100	nA
Collector Emitter Cutoff Current at $V_{CE} = 30\text{ V}$	I_{CES}	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	100	nA
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$ at $I_C = 1\text{ A}$, $I_B = 100\text{ mA}$	V_{CEsat}	- -	0.3 0.5	V
Base Emitter Saturation Voltage at $I_C = 1\text{ A}$, $I_B = 100\text{ mA}$	V_{BEsat}	-	1.2	V
Base Emitter Voltage at $I_C = 1\text{ A}$, $V_{CE} = 5\text{ V}$	V_{BE}	-	1.1	V
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	10	pF
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$, $f = 100\text{ MHz}$	f_T	150	-	MHz



Rating And Characteristic Curves

Fig.1 I_C - $V_{BE(on)}$
at $V_{CE} = 5V$, $T_a = 25^\circ C$

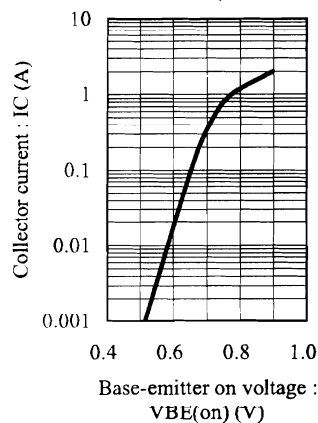


Fig.2 h_{FE} - I_C
at $V_{CE} = 5V$, $T_a = 25^\circ C$

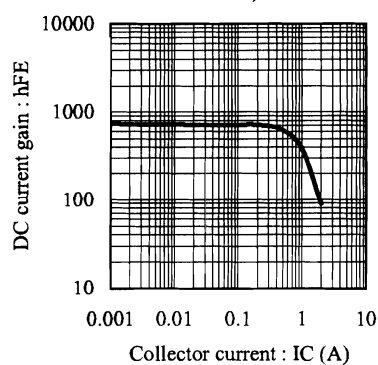


Fig.3 $V_{CE(sat)}$ - I_C
at $I_C/I_B = 10$, $T_a = 25^\circ C$

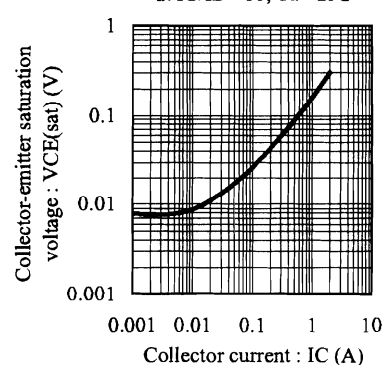


Fig.5 $V_{BE(sat)}$ - I_C
at $I_C/I_B = 10$, $T_a = 25^\circ C$

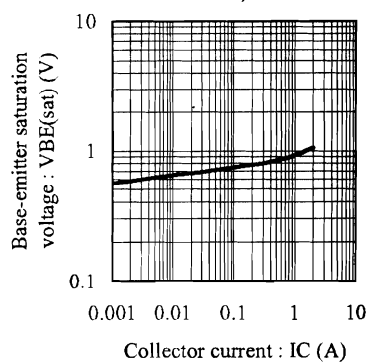


Fig.6 f_T - I_E
at $V_{CE} = 10V$, $T_a = 25^\circ C$

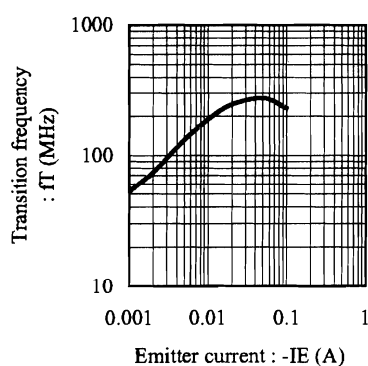


Fig.7 C_{ob} - V_{CB}
at $f = 1MHz$, $T_a = 25^\circ C$

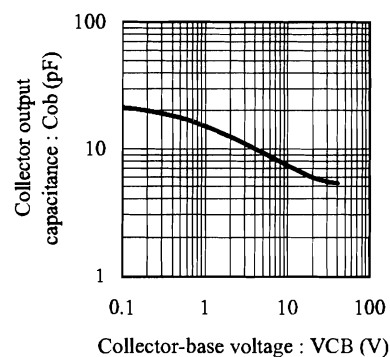
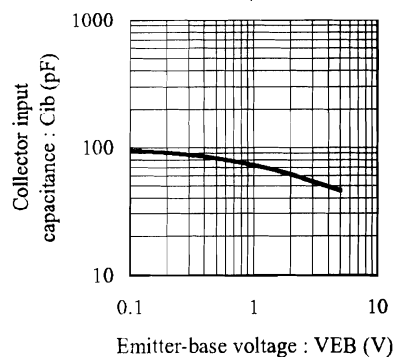


Fig.8 C_{ib} - V_{EB}
at $f = 1MHz$, $T_a = 25^\circ C$





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